

**HPP600R1K0DN****General Description:**

HPP600R1K0DN, the silicon N-channel Enhanced VDMOSFETs, is obtained by the double-shield Technology which reduce the conduction loss, improve switching performance and enhance the avalanche energy. The transistor can be used in various power switching circuit for system miniaturization and higher efficiency. The package form is TO-220AB, which accords with the RoHS standard.

Features:

- ! Superior switching performance
- ! Low on resistance($R_{dson} \leq 1\Omega$)
- ! Low gate charge (Typical Data:20.2nC)
- ! Low reverse transfer capacitances(Typical:17.8pF)
- ! 100% Single pulse avalanche energy test

Applications:

Power switch circuit of adaptor and charger.

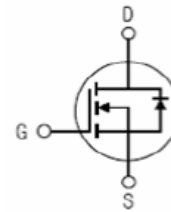
Absolute ($T_c = 25^\circ\text{C}$ unless otherwise specified):

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	600	V
I_D	Continuous Drain Current	6	A
	Continuous Drain Current $T_c = 100^\circ\text{C}$	3.6	A
I_{DM}^{a1}	Pulsed Drain Current	24	A
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	190	mJ
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	100	W
	Derating Factor above 25°C	0.8	W/ $^\circ\text{C}$
T_J, T_{stg}	Operating Junction and Storage Temperature Range	150, -55 to 150	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	300	$^\circ\text{C}$

V_{DSS}	600	V
I_D	6	A
$P_D(T_c=25^\circ\text{C})$	100	W
$R_{DS(ON)Typ}$	0.85	Ω

TO-220AB

1. Gate 2. Drain 3. Source

Inner Equivalent Principium Chart

Electrical Characteristics (Tc= 25°C unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	600	--	--	V
ΔBV _{DSS} /ΔT _J	Bvdss Temperature Coefficient	ID=250uA, Reference 25°C	--	0.66	--	V/°C
I _{DSS}	Drain to Source Leakage Current	V _{DS} =600V, V _{GS} = 0V, T _a = 25°C	--	--	1	μA
		V _{DS} =480V, V _{GS} = 0V, T _a = 125°C	--	--	100	μA
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} =+20V	--	--	100	nA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} =-20V	--	--	-100	nA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =3A	--	0.85	1	Ω
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	2.0	--	4.0	V
Pulse width tp ≤ 300μs, δ ≤ 2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g _{fs}	Forward Transconductance	V _{DS} =20V, I _D =3A	--	7.1	--	S
C _{iss}	Input Capacitance	V _{GS} = 0V V _{DS} = 25V f = 1.0MHz	--	1011	--	pF
C _{oss}	Output Capacitance		--	57.7	--	
C _{rss}	Reverse Transfer Capacitance		--	17.8	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D =6A V _{DD} = 300V R _G =10Ω V _{GS} =10V	--	17.9	--	ns
t _r	Rise Time		--	28.2	--	
t _{d(OFF)}	Turn-Off Delay Time		--	35.5	--	
t _f	Fall Time		--	13.8	--	
Q _g	Total Gate Charge	I _D =6A V _{DD} =480V V _{GS} = 10V	--	20.2	--	nC
Q _{gs}	Gate to Source Charge		--	4.6	--	
Q _{gd}	Gate to Drain ("Miller") Charge		--	8.7	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	6	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	24	A
V_{SD}	Diode Forward Voltage	$I_S=6A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=6A, T_J = 25^\circ C$ $dI_F/dt=100A/us,$ $V_{GS}=0V$	--	249	--	ns
Q_{rr}	Reverse Recovery Charge		--	1834	--	nC
I_{RRM}	Reverse Recovery Current		--	14.7	--	A
Pulse width $t_p \leq 300\mu s, \delta \leq 2\%$						

Symbol	Parameter	Max.	Units
$R_{\theta JC}$	Junction-to-Case	1.25	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	62.5	$^\circ C/W$

^{a1}: Repetitive rating; pulse width limited by maximum junction temperature

^{a2}: $L=20mH, I_D=4.4A, Start T_J=25^\circ C$

^{a3}: $I_{SD}=6A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}, Start T_J=25^\circ C$

Characteristics Curve:

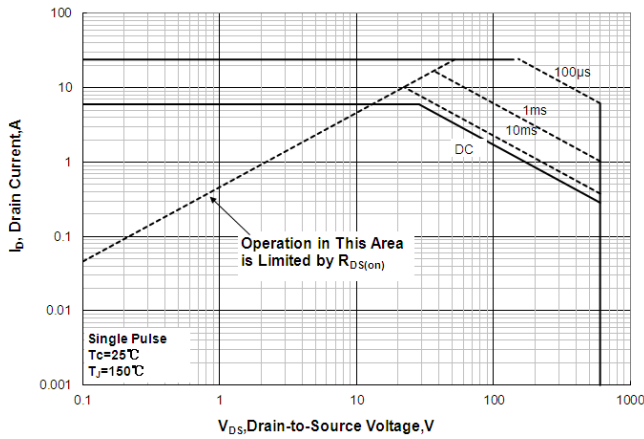


Figure 1 Maximum Forward Bias Safe Operating Area

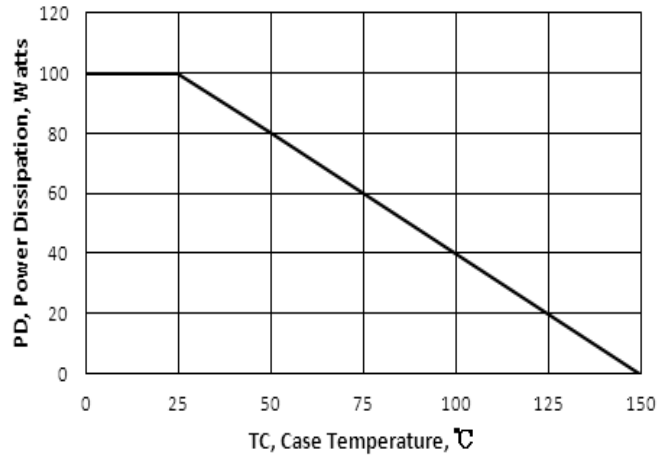


Figure 2 Maximum Power Dissipation vs Case Temperature

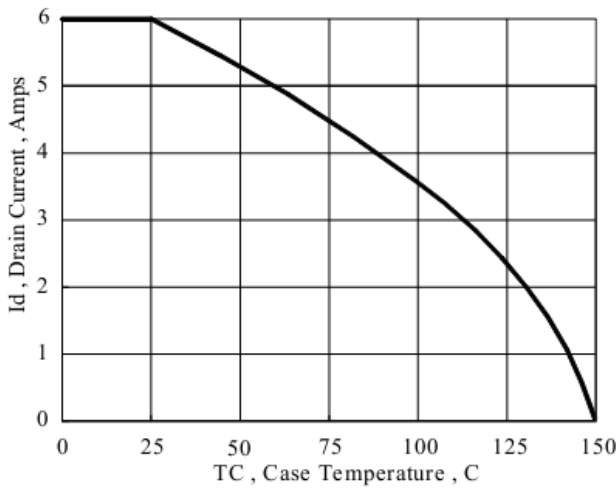


Figure 3 Maximum Continuous Drain Current vs Case Temperature

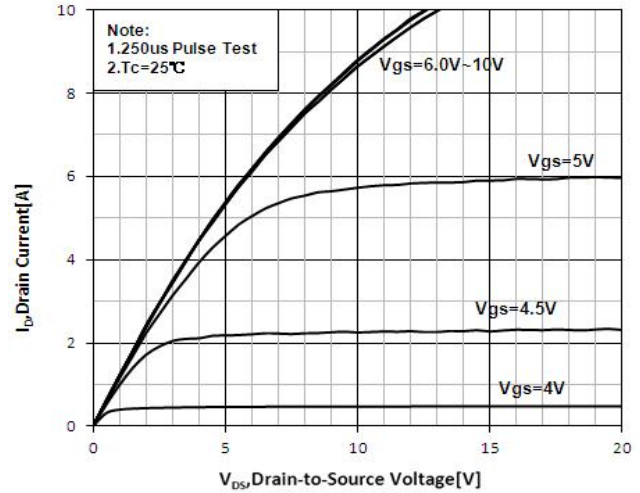


Figure 4 Typical Output Characteristics

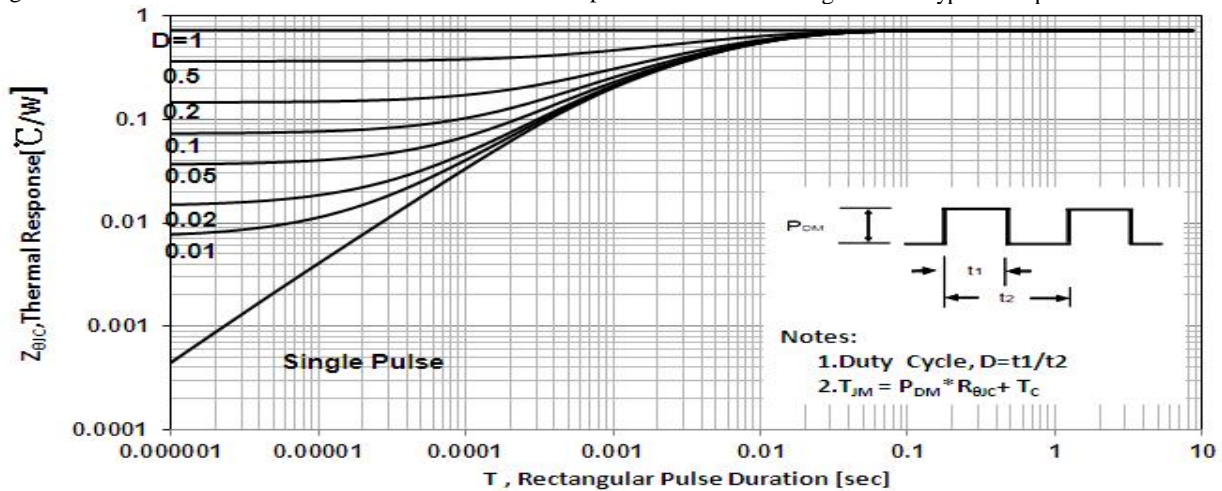


Figure 5 Maximum Effective Thermal Impedance, Junction to Case

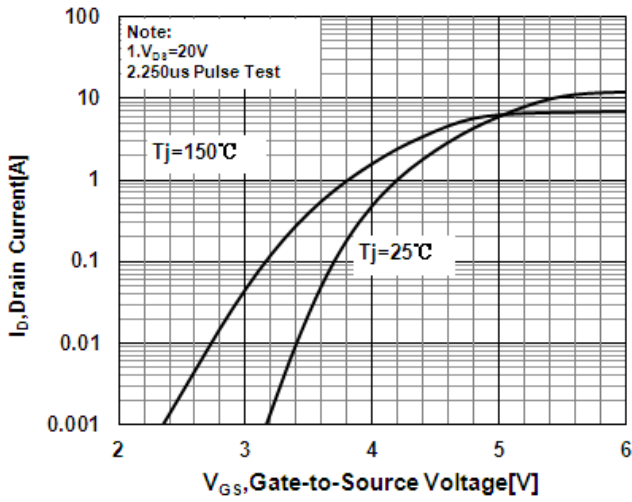


Figure 6 Typical Transfer Characteristics

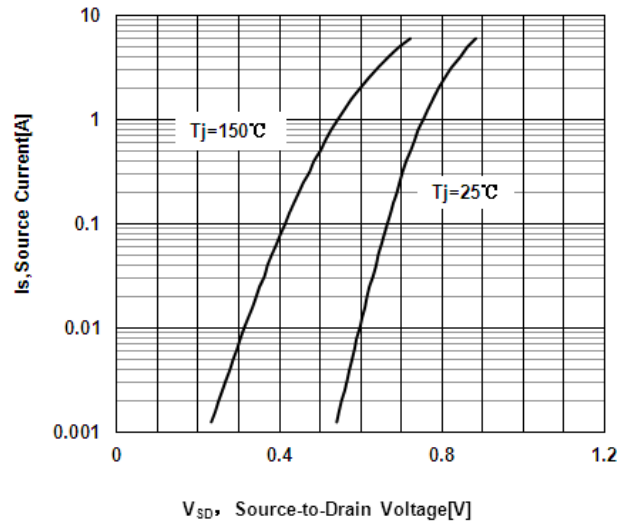


Figure 7 Typical Body Diode Transfer Characteristics

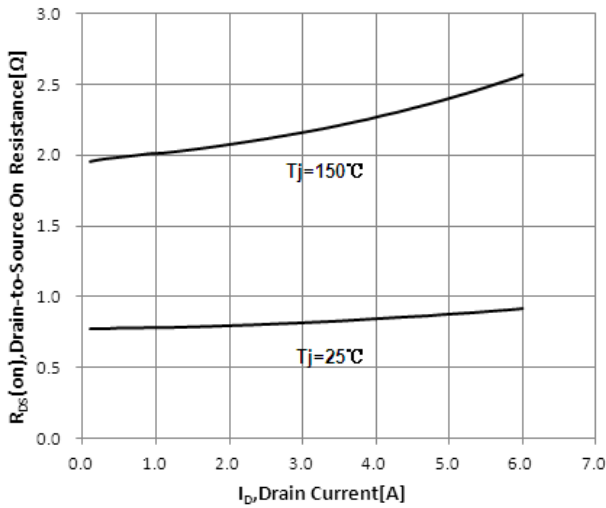


Figure 8 Typical Drain to Source ON Resistance vs Drain Current

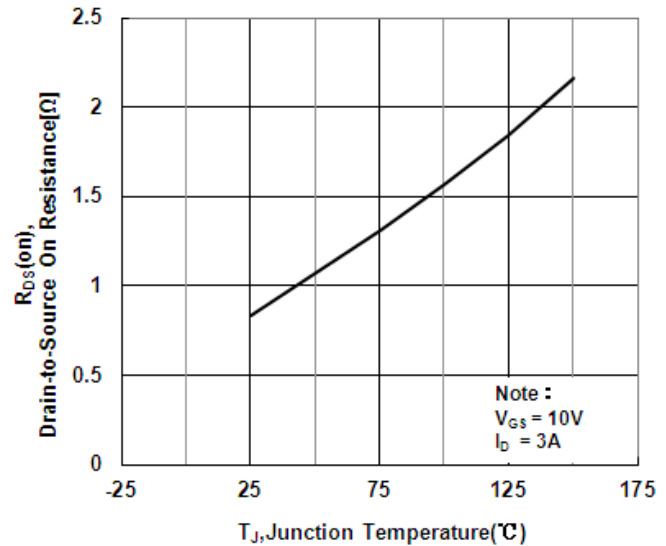


Figure 9 Typical Drain to Source on Resistance vs Junction Temperature

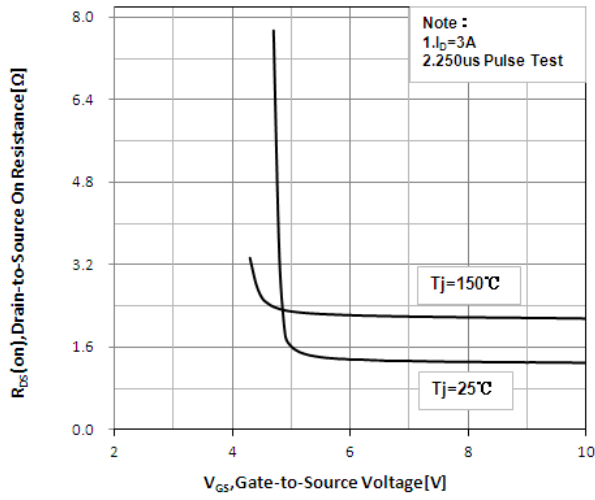


Figure 10 Drain to Source ON Resistance vs Gate-to-Source Voltage

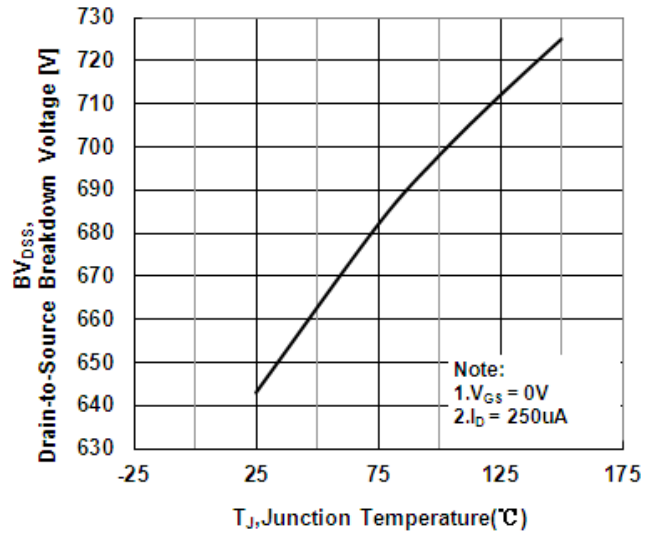


Figure 11 Typical Breakdown Voltage vs Junction Temperature

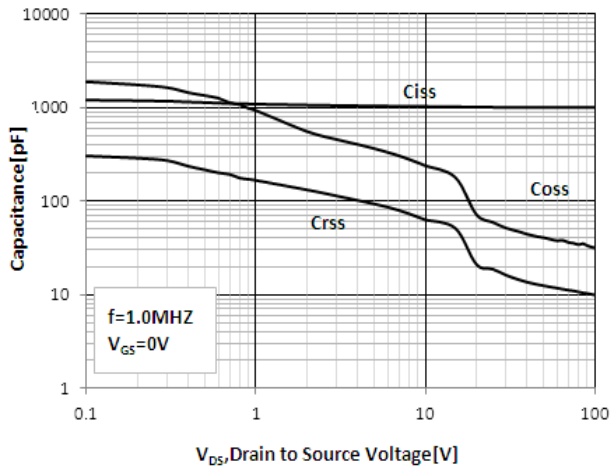


Figure 12 Typical Capacitance vs Drain to Source Voltage

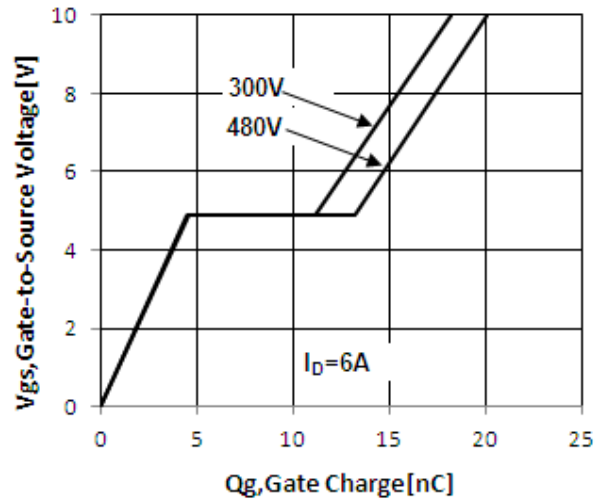


Figure 13 Typical Gate Charge vs Gate to Source Voltage

Test Circuit and Waveform

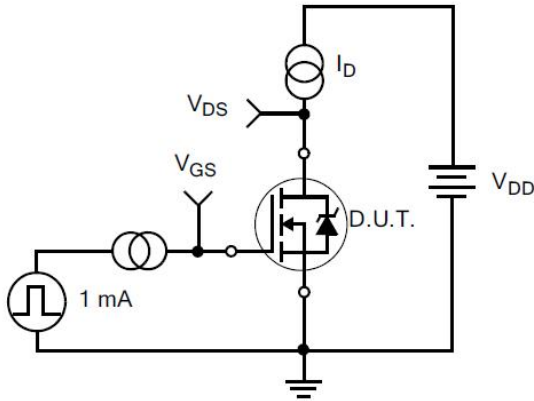


Figure 14. Gate Charge Test Circuit

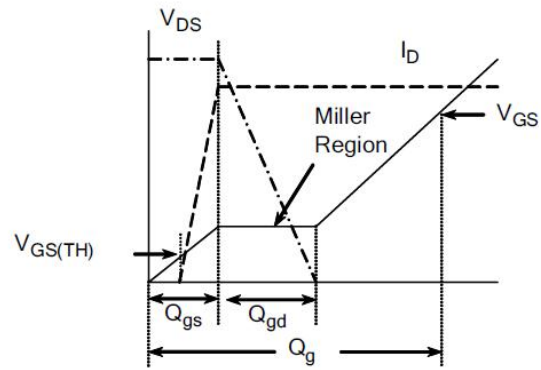


Figure 15. Gate Charge Waveforms

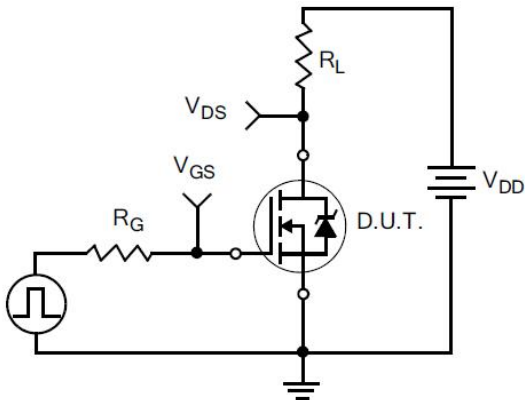


Figure 16. Resistive Switching Test Circuit

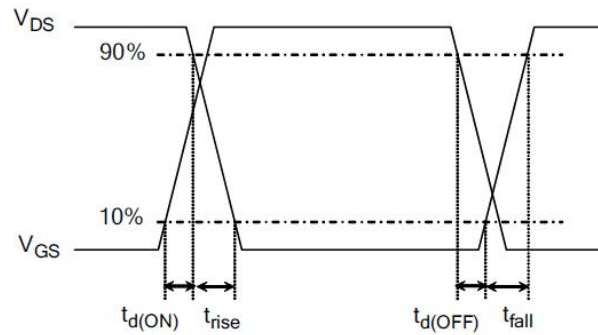
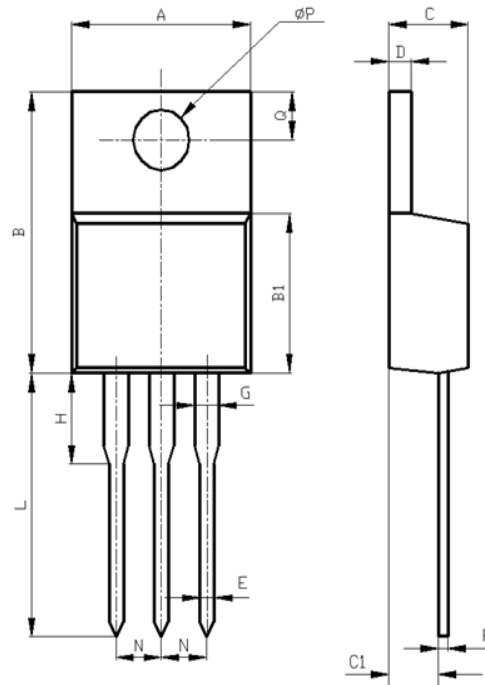


Figure 17. Resistive Switching Waveforms

Package Information



Items	Values(mm)	
	MIN	MAX
A	9.60	10.6
B	15.0	16.0
B1	8.90	9.50
C	4.30	4.80
C1	2.30	3.10
D	1.20	1.40
E	0.70	0.90
F	0.30	0.60
G	1.17	1.37
H	2.70	3.80
L*	12.6	14.8
N	2.34	2.74
Q	2.40	3.00
φ P	3.50	3.90

*adjustable

TO-220AB Package

